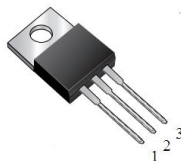
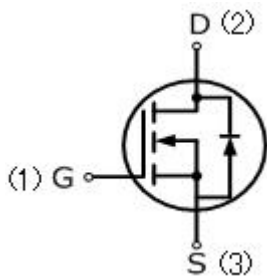


75N08(F,B,H)

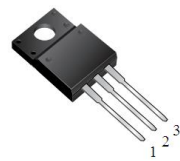
75A mps,80 Volts N-CHANNEL MOSFET

FEATURE

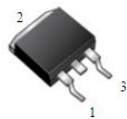
- 75A,80V, $R_{DS(ON)}=17m\Omega @V_{GS}=10V/35A$
- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220AB
75N08



ITO-220AB
75N08F



TO-263
75N08B



TO-263
75N08H

Absolute Maximum Ratings($T_C=25^\circ C$, unless otherwise noted)

Parameter	Symbol	75N08	UNIT
Drain-Source Voltage	V_{DSS}	80	V
Gate-Source Voltage	V_{GSS}	± 20	
Continuous Drain Current	I_D	75	A
Pulsed Drain Current(Note 1)	I_{DM}	300	
Single Pulse Avalanche Energy (Note 2)	E_{AS}	1550	mJ
Avalanche Current(Note 1)	I_{AR}	70	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	15.5	mJ
Reverse Diode dV/dt (Note 3)	dv/dt	7.0	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ C$
Mounting Torque	6-32 or M3 screw	10	lbf • in
		1.1	N • m

Thermal Characteristics

Parameter	Symbol	ITO-220	TO-220	TO-262 TO-263	Units
Maximum Junction-to-Case	R_{thJC}	1.6	0.8	0.8	$^\circ C/W$
Maximum Power Dissipation	P_D	78	156	156	W

Electrical Characteristics ($T_c=25^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Mix	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80	—	—	V
Breakdown Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_J$	Reference to 25°C , $I_D=250\mu A$	—	0.08	—	$V/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V$	—	—	1	μA
Gate-Body Leakage Current, Forward	I_{GSSF}	$V_{GS}=20V, V_{DS}=0V$	—	—	100	nA
Gate-Body Leakage Current, Reverse	I_{GSSR}	$V_{GS}=-20V, V_{DS}=0V$	—	—	-100	nA
On Characteristics						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=10V, I_D=250\mu A$	2.0	—	4.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=35A$	—	—	17	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{MHZ}$	—	2100	2700	pF
Output Capacitance	C_{oss}		—	790	1030	pF
Reverse Transfer Capacitance	C_{rss}		—	180	230	pF
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=40V, I_D=75A,$ $R_g=25\Omega$ (Note4,5)	—	25	60	ns
Turn-On Rise Time	t_r		—	300	610	ns
Turn-Off Delay Time	$t_{d(off)}$		—	90	190	ns
Turn-Off Fall Time	t_f		—	145	300	ns
Total Gate Charge	Q_g	$V_{DS}=60V, I_D=75A,$ $V_{GS}=10V,$ (Note4,5)	—	75	98	nC
Gate-Source Charge	Q_{gs}		—	14	—	nC
Gate-Drain Charge	Q_{gd}		—	37	—	nC
Drain-Source Body Diode Characteristics and Maximum Ratings						
Continuous Diode Forward Current	I_S		—	—	75	A
Pulsed Diode Forward Current	I_{SM}		—	—	300	A
Diode Forward Voltage	V_{SD}	$I_S=75A, V_{GS}=0V$	—	—	1.5	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_S=75A,$	—	84	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_F/dt=100A/\mu s,$ (Note4)	—	250	—	μC

Notes

1. Repetitive Rating: pulse width limited by maximum junction temperature.
2. $V_{DD}=20V$, starting, $L=0.4\text{mH}, R_g=25\Omega, I_{AS}=75A, T_J=25^\circ\text{C}$.
3. $I_{SD} \leq I_D, dI/dt = _A/\mu s, V_{DD} \leq BV_{DSS}$, starting $T_J=25^\circ\text{C}$.
4. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
5. Repetitive rating; pulse width limited by maximum junction temperature.